

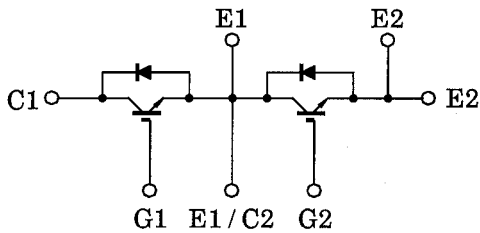
TOSHIBA GTR Module Silicon N Channel IGBT

MG300Q2YS50

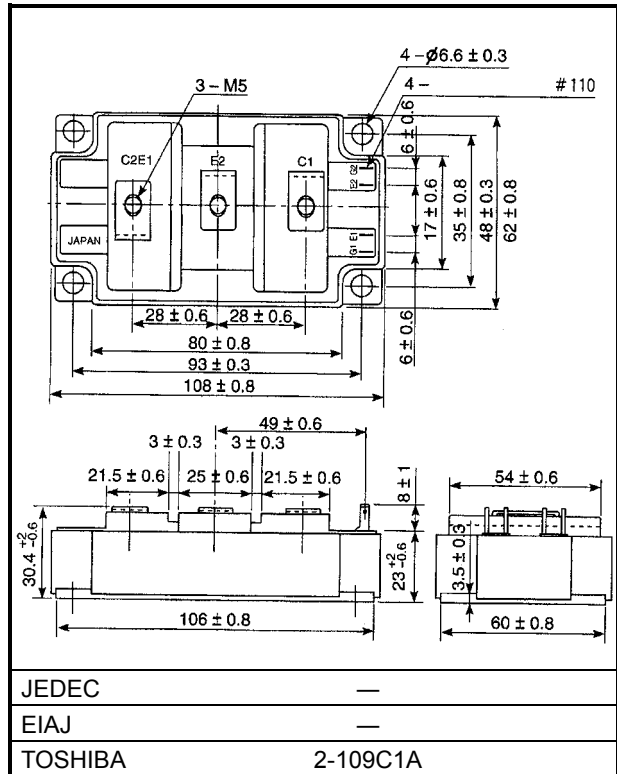
High Power Switching Applications
 Motor Control Applications

- High input impedance
- High speed : $t_f = 0.3\mu s$ (Max.)
 Inductive load
- Low saturation voltage
 : $V_{CE(sat)} = 3.6V$ (Max.)
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

Equivalent Circuit



Unit: mm



Weight: 430g

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-emitter voltage		V_{CES}	1200	V
Gate-emitter voltage		V_{GES}	±20	V
Collector current	DC	I_C (25°C / 80°C)	400 / 300	A
	1ms	I_{CP} (25°C / 80°C)	800 / 600	
Forward current	DC	I_F	300	A
	1ms	I_{FM}	600	
Collector power dissipation (Tc = 25°C)		P_C	2000	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-40 ~ 125	°C
Isolation voltage		V_{isol}	2500 (AC 1 minute)	V
Screw torque (Terminal / mounting)		—	3 / 3	N·m

Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	±500	nA	
Collector cut-off current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA	
Gate-emitter cut-off voltage		$V_{GE (OFF)}$	$I_C = 300mA, V_{CE} = 5V$	3.0	—	6.0	V	
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 300A,$ $V_{GE} = 15V$	$T_j = 25^\circ C$	—	2.8	3.6	V
				$T_j = 125^\circ C$	—	3.1	4.0	
Input capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	30.0	—	nF	
Switching time	Turn-on delay time	$t_{d (on)}$	Inductive load $V_{CC} = 600V$ $I_C = 300A$ $V_{GE} = \pm 15V$ $R_G = 2.7\Omega$ (Note 1)	—	0.05	—	μs	
	Rise time	t_r		—	0.05	—		
	Turn-on time	t_{on}		—	0.2	—		
	Turn-off delay time	$t_{d (off)}$		—	0.5	—		
	Fall time	t_f		—	0.1	0.3		
	Turn-off time	t_{off}		—	0.6	—		
Forward voltage		V_F	$I_F = 300 A, V_{GE} = 0$	—	2.4	3.5	V	
Reverse recovery time		t_{rr}	$I_F = 300 A, V_{GE} = -10 V,$ $di / dt = 1000 A / \mu s$ (Note 1)	—	0.2	0.3	μs	
Thermal resistance		$R_{th (j-c)}$	Transistor stage	—	—	0.06	°C / W	
			Diode stage	—	—	0.19		